

Application Data Sheet

Inventor Information

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Correspondence Information

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Application Information

Title: STATIC RANDOM ACCESS MEMORY AND
SEMICONDUCTOR DEVICE USING MOS TRANSISTORS
HAVING CHANNEL REGION ELECTRICALLY CONNECTED
WITH GATE
Total Drawing Sheets: 5
Formal Drawings: Yes
Application Type: Utility
Docket Number: 204552016501

Representative Information

Representative Customer Number: 25227

Continuity Information

This application is a: Continuation
Of application: 09/412,328

Filed:

10/5/1999

Prior Foreign Applications

Foreign Application:	10-282335
Filing Date:	10/05/1998
Country:	Japan
Priority Claimed:	Yes

Assignee Information

Company Name:	Sharp Kabushiki Kaisha
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